Attorney Reference No.: SAM-0465

Declaration, Petition and Power of Attorney for Patent Application

As a below named inventor, I hereby declare that:

My residence, mailing address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

METHOD FOR MANUFACTURIN() MULTI-THICKNESS GATE DI-ELECTRIC LAYER OF SEMICONDUCTOR DEVICE

the specification	of which (check only one):
<u>X</u>	is attached hereto; or
	was filed as United States or PCT International Application Serial No on and was amended on (if applicable).

I hereby state that I have reviewed and understand the contents of the specification, including the claims as amended by any amendment referred to herein.

I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Title 37 C.F.R. §1.56, including for continuation-in-part applications, material information which became available between the filing date of the prior application and the national or PCT international filing date of the continuation-in-part application.

I hereby claim foreign priority benefits under 35 U.S.C. §119(a)-(d) or (f), or §365(b) of any foreign application(s) for patent or inventor's certificate or §365(a) of any PCT international application(s) designating at least one country other than the United States of America listed below and have also identified below any foreign application(s) for patent or inventor's certificate or any PCT international application(s) designating at least one country other than the United States of America filed by me on the same subject matter having a filing date before that of the application(s) of which priority is claimed.

Prior foreign/PCT application(s) and priority claims under 35 U.S.C. §119(a)-(d) or §365

Country	Application Number	Filing Date (day, month, year)
Korea	02-67545	1 November 2002

I hereby claim the benefit under 35 U.S.C. §119(e) of any United States provisional application(s) listed below.

Prior U.S. applications for benefit under 35 U.S.C. §119(e)

Application Number	Filing Date

I hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s) or PCT international application(s) designating the United States of America that is/are listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in that/those prior application(s) in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose material information as defined in 37 C.F.R. §1.56 which occurred between the filing date of the prior applications and the national or PCT international filing date of this application:

Prior U.S. Applications or PCT International Applications designating the U.S. for benefit under 35 U.S.C. § 120

Application Number	Filing Date (day, month, year)	Status (issued, pending, abandoned)

As a named inventor, I hereby appoint the following attorneys and/or agents to prosecute this application and transact all business in the Patent and Trademark Office connected therewith:

Steven M. Mills Reg. No. 36,610

Anthony P. Onello, Jr. Reg. No. 38,572

Send correspondence and direct telephone calls to:

Anthony P. Onello, Jr. MILLS & ONELLO LLP Eleven Beacon Street, Suite 605 Boston, Massachusetts 02108 phone: (617) 994-4900 facsimile: (617) 742-7774

Wherefore I petition that letters patent be granted to me for the invention or discovery described and claimed in the attached specification and claims, and hereby subscribe my name to said specification and claims and to the foregoing declaration, power of attorney, and this petition.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. 1001 and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

First Inventor

Family Name Kim	First Given Name Kyunit-soo	Second Given Name
City of Residence Euijeongbu-city, Gyeonggi-do	State or Foreign Country of Residence Republic of Korea	Country of Citizenship Republic of Korea
Post Office Address 507-706, Jangam Jukong 5-danji- Apt., Singok 1-dong	^{City} Euijeongbu-city, Gyeonggi-do	State & Zip Code/Country Republic of Korea
Signature Kyung-Soo,	Date Sep. 22. 2003	

	iomoy Reference No.: Brain 646.
First Given Name Young-wug	Second Given Name
State or Fareign Country of Residence Republic f Korea	Country of Critizenship Republic f Korea
City Kangnam-gu, Seoul	State & Zip Code/Country Republic of Korea
gkin	Date Sep. 22,2003
First Given Name Chang-bong	Second Given Name
State or Foreign Country of Residence Republic of Korea	Country of Chizenship Republic of Korea
City Seongnnam-city, Kyungki-do	State & Zip Code/Country Republic of Korea
ng Oh	Date Sep. 22th. 2003.
	'
First Given Name Hee-Stang	Second Given Name
State or Foreign Country of Residence Republic of Korea	Country of Citizenship Republic of Korea
City Seongnam-city, Gyeonggi-do	State & Zip Code/Country Republic of Korea
Kang.	Date Sep. 22. 2003
	/
First Given Name	Second Given Name
State or Fe-reign Country of Residence	Country of Citizenship
City Guri-city, Gyconggi-do	Republic of Korea State & Zip Code/Country Republic of Korea
	First Given Name Younty-wug State or Foreign Country of Residence Republic f Korea City Kangnam-gu, Seoul First Given Name Chanjs-bong State or Foreign Country of Residence Republic of Korea City Seongnam-city, Kyungki-do First Given Name Hee-sung State or Foreign Country of Residence Republic of Korea City Seongnam-city, Gyeonggi-do First Given Name Hee-sung State or Foreign Country of Residence Republic of Korea City Seongnam-city, Gyeonggi-do First Given Name Hee-sung State or Foreign Country of Residence Republic of Korea City Sinte or Foreign Country of Residence Republic of Korea City

J:\SAM\0465\Decpoa.wpd

Signature

Date